

General Description

The 845264 is a 3.3V, 2.5V CML clock generator designed for Ethernet applications. The device synthesizes four clock frequencies on two separately selectable output banks. Each bank has either a 62.5MHz, 125MHz, 156.25MHz or 312.5MHz clock signal with excellent phase jitter performance. Each clock frequency is distributed to two low-skew differential CML output banks with a total of four outputs. The device is suitable for driving the reference clocks of Ethernet PHYs. The device supports 3.3V and 2.5V voltage supply and is packaged in a small, lead-free (RoHS 6) 32-lead VFQFN package. The extended temperature range supports telecommunication, wireless infrastructure and networking end equipment requirements.

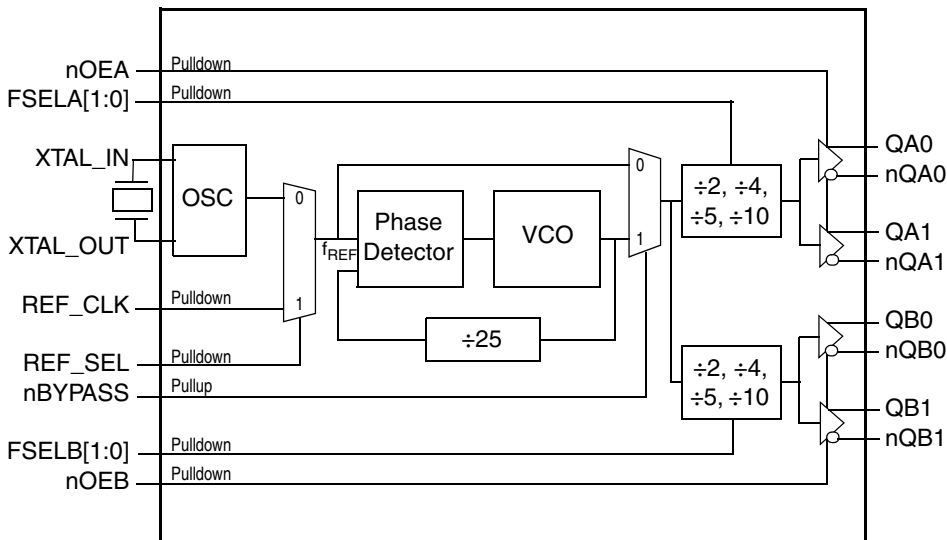
Features

- Clock generation of: 62.5MHz, 125MHz, 156.25MHz and 312.5MHz
- Two banks of two differential CML clock outputs
- Crystal interface designed for 25MHz, 12pF parallel resonant crystal
- RMS phase jitter @ 125MHz, using a 25MHz crystal (1.875MHz – 20MHz): 0.486ps (typical)

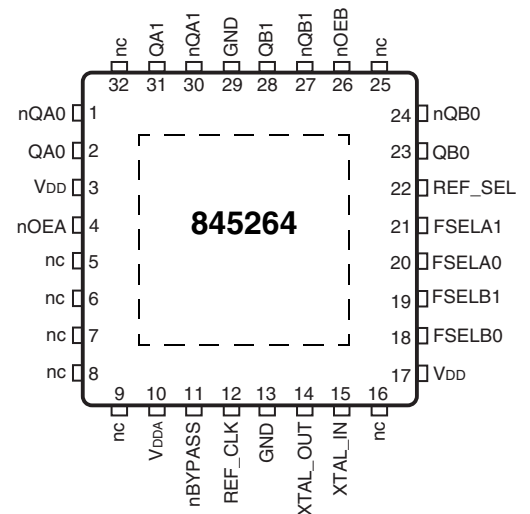
| Offset | Single-side Band Phase Noise |
|--------|------------------------------|
| 100Hz | -97 dBc/Hz |
| 1kHz | -118 dBc/Hz |
| 10kHz | -125 dBc/Hz |
| 100kHz | -123 dBc/Hz |

- LVCMOS interface levels for the control inputs
- Full 3.3V and 2.5V supply voltage
- Lead-free (RoHS 6) 32 VFQFN packaging
- -40°C to 85°C ambient operating temperature

Block Diagram



Pin Assignment



32 lead, 5mm x 5mm VFQFN

Pin Descriptions and Characteristics

Table 1. Pin Descriptions

| Number | Name | Type | | Description |
|---------------------------|-------------------|--------|----------|---|
| 1, 2 | nQA0, QA0 | Output | | Bank A differential clock output pair. CML interface levels. |
| 3, 17 | V _{DD} | Power | | Core supply pins. |
| 4 | nOEA | Input | Pulldown | Output enable pin for Bank A outputs. See Table 3E for function. LVCMOS/LVTTL interface levels. |
| 5, 6, 7, 8, 9, 16, 25, 32 | nc | Unused | | Do not connect. |
| 10 | V _{DDA} | Power | | Analog supply pin. |
| 11 | nBYPASS | Input | Pullup | PLL bypass pin. See Table 3D for function. LVCMOS/LVTTL interface levels. |
| 12 | REF_CLK | Input | Pulldown | Single-ended reference clock input. LVCMOS/LVTTL interface levels. |
| 13, 29 | GND | Power | | Power supply ground. |
| 14, 15 | XTAL_OUT, XTAL_IN | Input | | Crystal oscillator interface. XTAL_IN is the input, XTAL_OUT is the output. |
| 18, 19 | FSELB0, FSELB1 | Input | Pulldown | Output frequency divider select enable pins for Bank B outputs. See Table 3C for function. LVCMOS/LVTTL interface levels. |
| 20, 21 | FSELA0, FSELA1 | Input | Pulldown | Output frequency divider select enable pins for Bank A outputs. See Table 3B for function. LVCMOS/LVTTL interface levels. |
| 22 | REF_SEL | Input | Pulldown | PLL reference clock select pin. See Table 3A for function. LVCMOS/LVTTL interface levels. |
| 23, 24 | QB0, nQB0 | Output | | Bank B differential clock output pair. CML interface levels. |
| 26 | nOEB | Input | Pulldown | Output enable pin for Bank B outputs. See Table 3F for function. LVCMOS/LVTTL interface levels. |
| 27, 28 | nQB1, QB1 | Output | | Bank B differential clock output pair. CML interface levels. |
| 30, 31 | nQA1, QA1 | Output | | Bank A differential clock output pair. CML interface levels. |

NOTE: *Pulldown* and *Pullup* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|-------------------------|--|---------|---------|---------|-------|
| C _{IN} | Input Capacitance | nBYPASS, REF_SEL, nOEA, nOEB, FSELB0, FSELB1, FSELA0, FSELA1 | | 4 | | pF |
| R _{PULLDOWN} | Input Pulldown Resistor | | | 51 | | kΩ |
| R _{PULLUP} | Input Pullup Resistor | | | 51 | | kΩ |

Function Tables

Table 3A. PLL Reference Clock Select Function Table

| Input | Operation |
|-------------|--|
| REF_SEL | |
| 0 (default) | The crystal interface is the selected reference clock. |
| 1 | The REF_CLK input is the selected reference clock. |

NOTE: REF_SEL is an asynchronous control.

Table 3B. FSELA[1:0] Output Divider Select Function Table

| Input | | Operation | Output Frequency |
|-------------|-------------|-----------|------------------|
| FSELA1 | FSELA0 | | |
| 0 (default) | 0 (default) | ÷ 2 | 312.5MHz |
| 0 | 1 | ÷ 4 | 156.25MHz |
| 1 | 0 | ÷ 5 | 125MHz |
| 1 | 1 | ÷ 10 | 62.5MHz |

NOTE: FSELA[1:0] are asynchronous controls. Using 25MHz input reference.

Table 3C. FSELB[1:0] Output Divider Select Function Table

| Input | | Operation | Output Frequency |
|-------------|-------------|-----------|------------------|
| FSELB1 | FSELB0 | | |
| 0 (default) | 0 (default) | ÷ 2 | 312.5MHz |
| 0 | 1 | ÷ 4 | 156.25MHz |
| 1 | 0 | ÷ 5 | 125MHz |
| 1 | 1 | ÷ 10 | 62.5MHz |

NOTE: FSELB[1:0] are asynchronous controls. Using 25MHz input reference.

Table 3D. PLL nBYPASS Function Table

| Input | |
|-------------|---|
| nBYPASS | Operation |
| 0 | PLL is bypassed. The reference frequency f_{REF} is divided by the selected output divider. AC specifications do not apply in PLL bypass mode. |
| 1 (default) | PLL is enabled. The reference frequency f_{REF} is multiplied by the selected feedback divider and then divided by the selected output divider. |

NOTE: nBYPASS is an asynchronous control.

Table 3E. Output Enable Function Table

| Input | |
|-------------|--|
| nOEA | Operation |
| 0 (default) | QA[1:0], nQA[1:0] Outputs enabled. |
| 1 | QA[1:0], nQA[1:0] Outputs disabled (high-impedance). |

NOTE: nOEA is an asynchronous control.

Table 3F. Output Enable Function Table

| Input | |
|-------------|--|
| nOEB | Operation |
| 0 (default) | QB[1:0], nQB[1:0] Outputs enabled. |
| 1 | QB[1:0], nQB[1:0] Outputs disabled (high-impedance). |

NOTE: nOEB is an asynchronous control.

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item | Rating |
|--|--|
| Supply Voltage, V_{DD} | 4.6V |
| Inputs, V_I XTAL_IN Other Inputs | 0V to V_{DD} -0.5V to $V_{DD} + 0.5V$ |
| Outputs, I_O | -0.5V to $V_{DD} + 0.5V$ |
| Package Thermal Impedance, θ_{JA} | 43.4°C/W (0 mps) |
| Storage Temperature, T_{STG} | -65°C to 150°C |

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-----------------------|-----------------|-----------------|---------|----------|-------|
| V_{DD} | Core Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{DDA} | Analog Supply Voltage | | $V_{DD} - 0.12$ | 3.3 | V_{DD} | V |
| I_{DD} | Power Supply Current | | | 71 | 89 | mA |
| I_{DDA} | Analog Supply Current | | | 9 | 12 | mA |

Table 4B. Power Supply DC Characteristics, $V_{DD} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-----------------------|-----------------|-----------------|---------|----------|-------|
| V_{DD} | Core Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| V_{DDA} | Analog Supply Voltage | | $V_{DD} - 0.11$ | 2.5 | V_{DD} | V |
| I_{DD} | Power Supply Current | | | 68 | 84 | mA |
| I_{DDA} | Analog Supply Current | | | 8 | 11 | mA |

Table 4C. LVCMOS/LVTTL Input DC Characteristics, $V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|--------------------|--|--|---------|---------|----------------|---------|
| V_{IH} | Input High Voltage | | $V_{DD} = 3.3V$ | 2.2 | | $V_{DD} + 0.3$ | V |
| | | | $V_{DD} = 2.5V$ | 1.7 | | $V_{DD} + 0.3$ | V |
| V_{IL} | Input Low Voltage | | $V_{DD} = 3.3V$ | -0.3 | | 0.8 | V |
| | | | $V_{DD} = 2.5V$ | -0.3 | | 0.7 | V |
| I_{IH} | Input High Current | nOEA, nOEB, FSELA[1:0], FSELB[1:0], REF_SEL, REF_CLK | $V_{DD} = V_{IN} = 3.465V$ or $2.625V$ | | | 150 | μA |
| | | nBYPASS | $V_{DD} = V_{IN} = 3.465V$ or $2.625V$ | | | 5 | μA |
| I_{IL} | Input Low Current | nOEA, nOEB, FSELA[1:0], FSELB[1:0], REF_SEL, REF_CLK | $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -5 | | | μA |
| | | nBYPASS | $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -150 | | | μA |

Table 4D. CML DC Characteristics, $V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|-----------------------------------|-----------------|-----------------|-----------------|----------|-------|
| V_{OH} | Output High Voltage; NOTE 1 | | $V_{DD} - 0.02$ | $V_{DD} - 0.01$ | V_{DD} | V |
| V_{OUT} | Output Voltage Swing | | 300 | 480 | 600 | mV |
| V_{DIFF_OUT} | Differential Output Voltage Swing | | 600 | 960 | 1200 | mV |

NOTE 1: Outputs are terminated with 50Ω to V_{DD} .

Table 5. Crystal Characteristics

| Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|------------------------------------|-----------------|-------------|---------|---------|----------|
| Mode of Oscillation | | Fundamental | | | |
| Frequency | | | 25 | | MHz |
| Equivalent Series Resistance (ESR) | | | | 50 | Ω |
| Shunt Capacitance (C_O) | | | | 7 | pF |
| Load Capacitance (C_L) | | | | 12 | pF |

AC Characteristics

Table 6. AC Characteristics, $V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Parameter | Symbol | Test Conditions | Minimum | Typical | Maximum | Units |
|----------------------|--------------------------------|---|---------|---------|---------|-------|
| f_{OUT} | Output Frequency; NOTE 1 | FSELx[1:0] = 00 | | 312.5 | | MHz |
| | | FSELx[1:0] = 01 | | 156.25 | | MHz |
| | | FSELx[1:0] = 10 | | 125 | | MHz |
| | | FSELx[1:0] = 11 | | 62.5 | | MHz |
| tsk(o) | Output Skew; NOTE 1, 2, 3 | | | | 80 | ps |
| tsk(b) | Bank Skew; NOTE 1, 3, 4 | | | | 30 | ps |
| $f_{jit}(\emptyset)$ | RMS Phase Jitter; NOTE 5, 6 | 125MHz, Integration Range: 1.875MHz – 20MHz | | 0.486 | | ps |
| | | 156.25MHz, Integration Range: 1.875MHz – 20MHz | | 0.427 | | ps |
| t_R / t_F | Output Rise/Fall Time | 20% to 80% | 300 | 480 | 800 | ps |
| odc | Output Duty Cycle | | 45 | 50 | 55 | % |

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: $f_{REF} = 25\text{MHz}$. Outputs are terminated with 50Ω to V_{DD} . (FOX 277LF-25-99, 12pF, 25MHz crystal)

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential crosspoint.

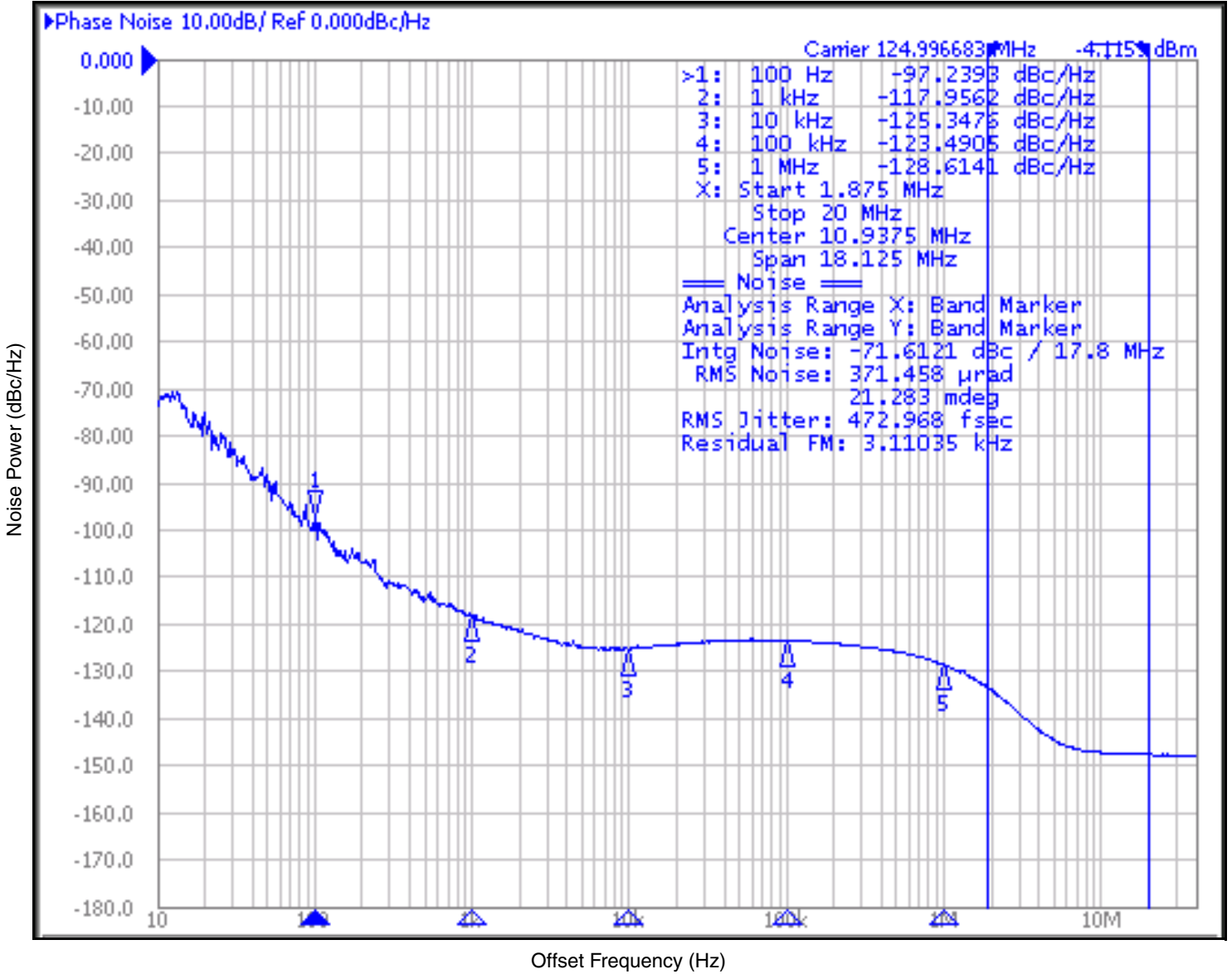
NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 4: Defined as skew within a bank of outputs at the same voltage and with equal load conditions.

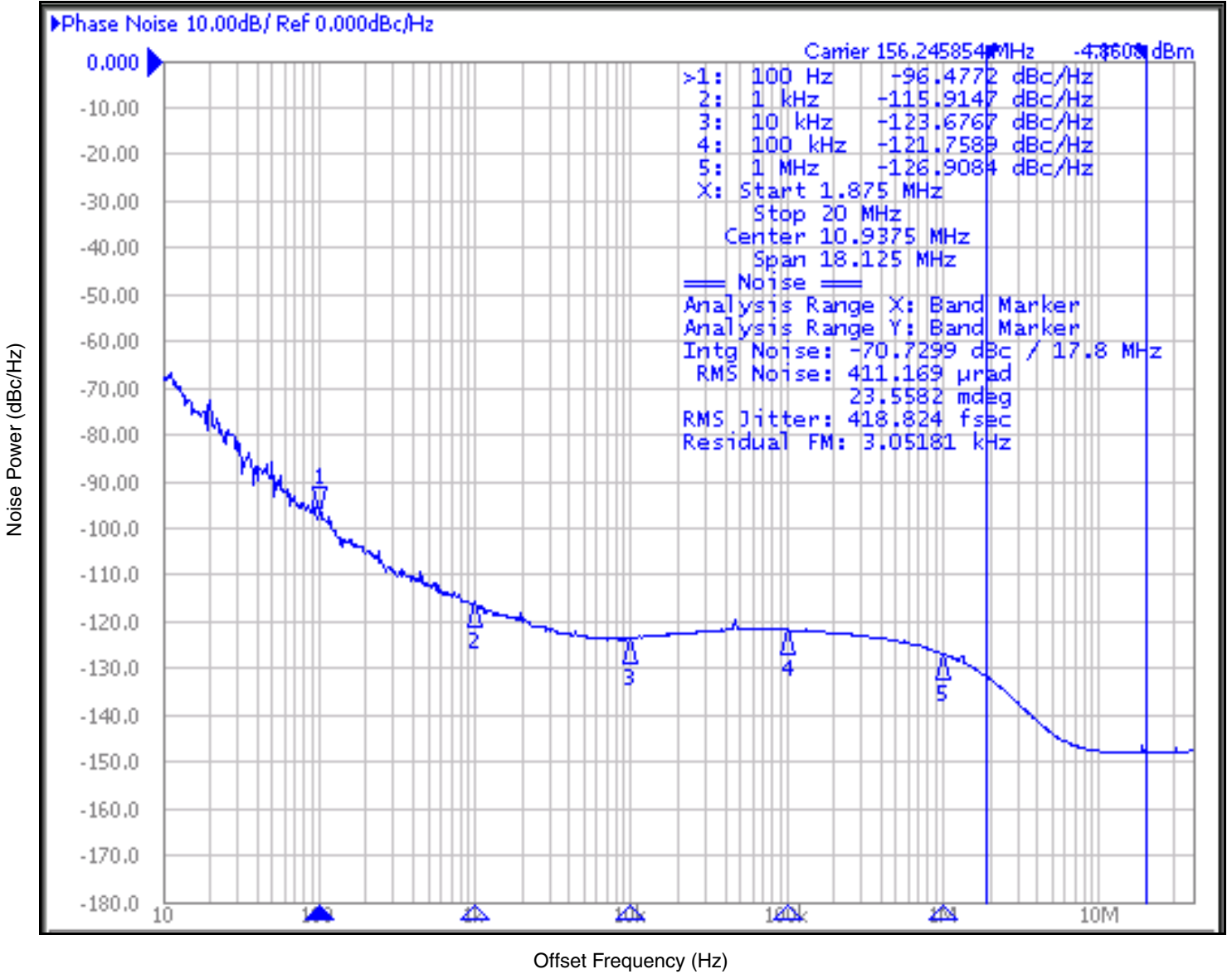
NOTE 5: Please refer to the phase noise plots.

NOTE 6: Data was taken with both outputs at the same frequency.

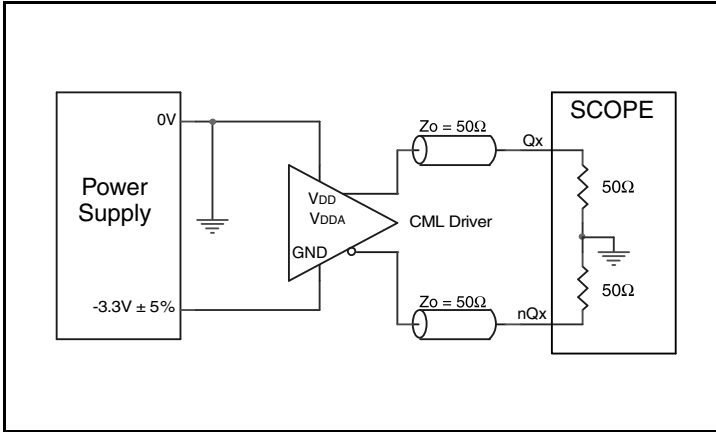
Typical Phase Noise at 125MHz



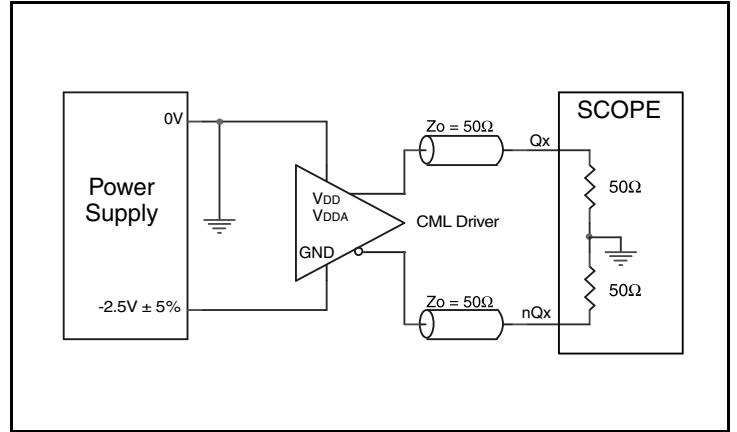
Typical Phase Noise at 156.25MHz



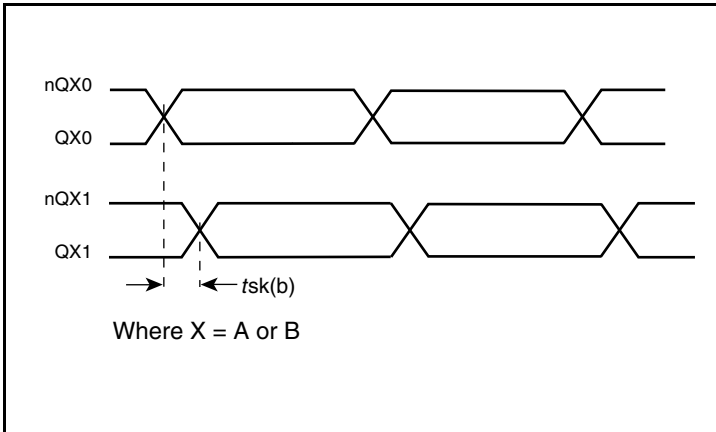
Parameter Measurement Information



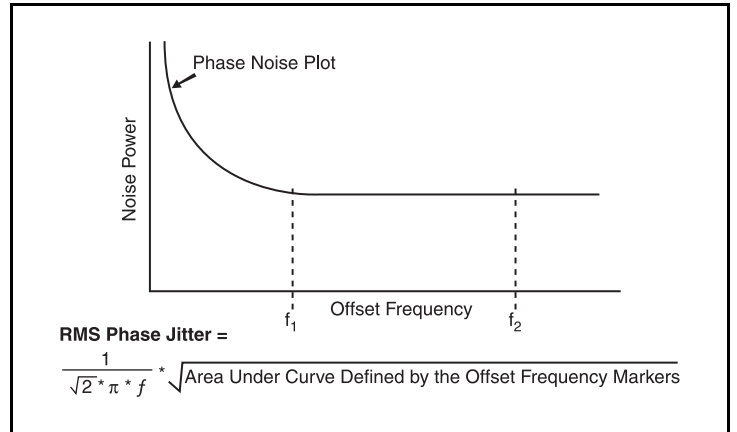
3.3V CML Output Load Test Circuit



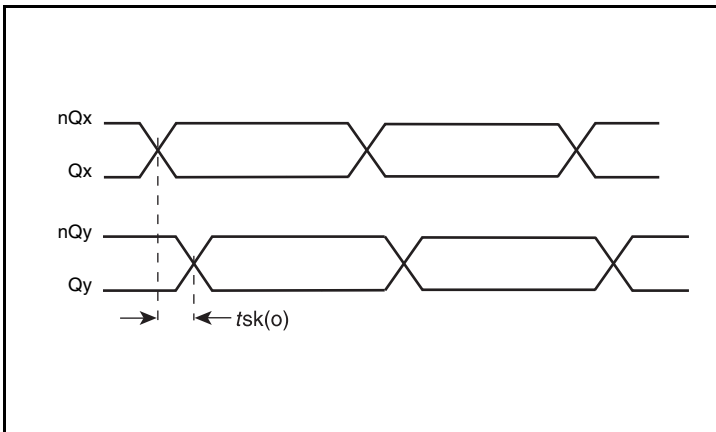
2.5V CML Output Load Test Circuit



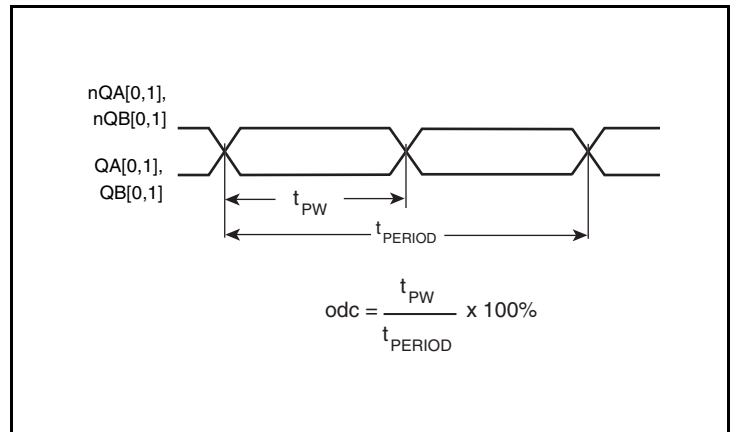
Bank Skew



RMS Phase Jitter

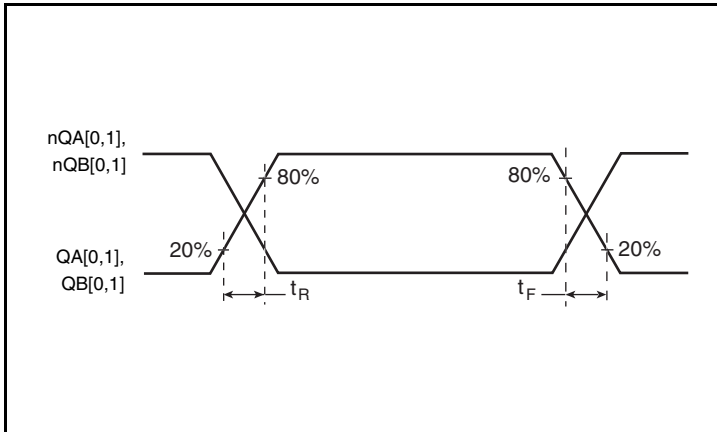


Output Skew

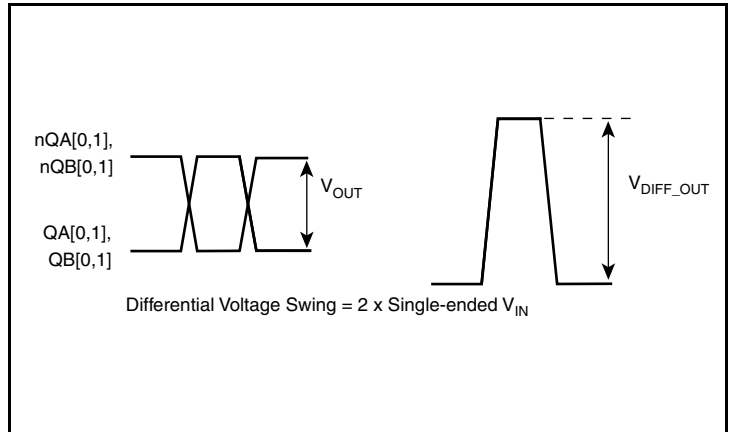


Output Duty Cycle/Pulse Width/Period

Parameter Measurement Information, continued



Output Rise/Fall Time



Differential Output Voltage Swing

Applications Information

Recommendations for Unused Input and Output Pins

Inputs:

LVC MOS Control Pins

All control pins have internal pullups and pulldowns; additional resistance is not required but can be added for additional protection. A 1k Ω resistor can be used.

REF_CLK Input

For applications not requiring the use of the reference clock, it can be left floating. Though not required, but for additional protection, a 1k Ω resistor can be tied from the REF_CLK to ground.

Outputs:

CML Outputs

All unused CML outputs can be left floating. We recommend that there is no trace attached. Both sides of the differential output pair should either be left floating or terminated.

Overdriving the XTAL Interface

The XTAL_IN input can be overdriven by an LVCMOS driver or by one side of a differential driver through an AC coupling capacitor. The XTAL_OUT pin can be left floating. The amplitude of the input signal should be between 500mV and 1.8V and the slew rate should not be less than 0.2V/ns. For 3.3V LVCMOS inputs, the amplitude must be reduced from full swing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. *Figure 1A* shows an example of the interface diagram for a high speed 3.3V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver (R_o) and the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This

can be done in one of two ways. First, R_1 and R_2 in parallel should equal the transmission line impedance. For most 50Ω applications, R_1 and R_2 can be 100Ω. This can also be accomplished by removing R_1 and changing R_2 to 50Ω. The values of the resistors can be increased to reduce the loading for a slower and weaker LVCMOS driver. *Figure 1B* shows an example of the interface diagram for an LVPECL driver. This is a standard LVPECL termination with one side of the driver feeding the XTAL_IN input. It is recommended that all components in the schematics be placed in the layout. Though some components might not be used, they can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a quartz crystal as the input.

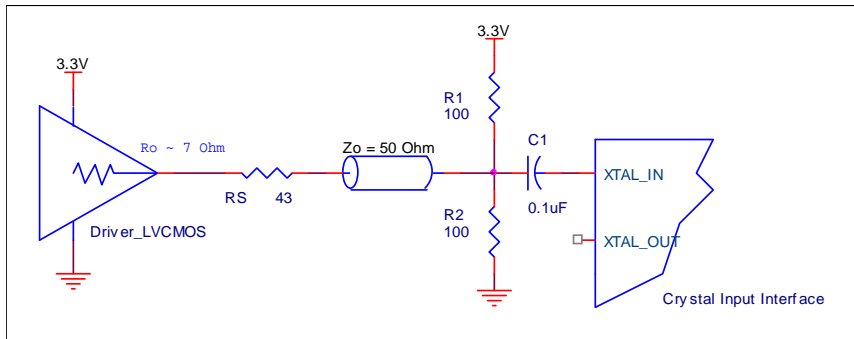


Figure 1A. General Diagram for LVCMOS Driver to XTAL Input Interface

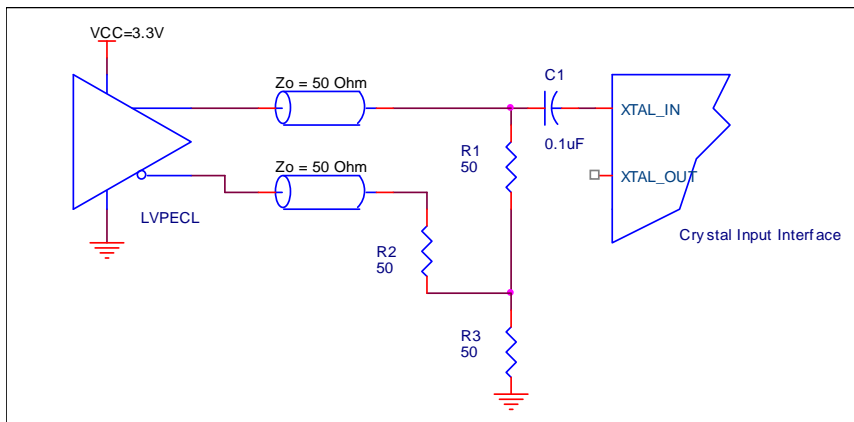


Figure 1B. General Diagram for LVPECL Driver to XTAL Input Interface

VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 2*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor’s Thermally/Electrically Enhance Leadframe Base Package, Amkor Technology.

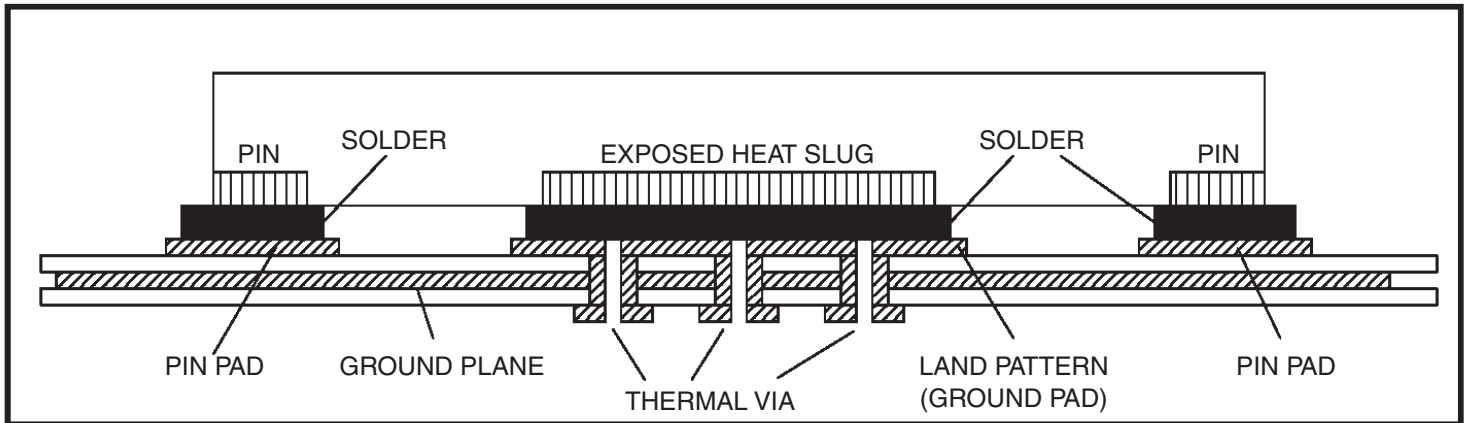


Figure 2. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)

Schematic Example

Figure 3 shows an example of 845264 application schematic. In this example, the device is operated at $V_{DD} = V_{DDA} = 3.3V$. The schematic example focuses on functional connections and is not configuration specific. Refer to the pin description and functional tables in the datasheet to ensure that the logic control inputs are properly set.

A 12pF parallel resonant 25MHz crystal is used. For this device, the crystal load capacitors are required for proper operation. The load capacitance, $C1 = C2 = 2pF$, are recommended for frequency accuracy. Depending on the variation of the parasitic stray capacity of the printed circuit board traces between the crystal and the XTAL_IN and XTAL_OUT pins, the values of C1 and C2 might require a slight adjustment to optimize the frequency accuracy. Crystals with other load capacitance specifications can be used, but this will require adjusting C1 and C2. When designing the circuit board, return the capacitors to ground through a single point contact close to the package. Two Fox crystal options are shown in the schematic for design flexibility.

The ePAD provides a low thermal impedance connection between the internal device and the PCB. It also provides an electrical connection to the die and must be connected to ground.

As with any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The 845264 provides separate power supplies to isolate any high switching noise from coupling into the internal PLL.

In order to achieve the best possible filtering, it is recommended that the placement of the filter components be on the device side of the PCB as close to the power pins as possible. If space is limited, the 0.1uF capacitor in each power pin filter should be placed on the device side. The other components can be on the opposite side of the PCB.

Power supply filter recommendations are a general guideline to be used for reducing external noise from coupling into the devices. The filter performance is designed for a wide range of noise frequencies. This low-pass filter starts to attenuate noise at approximately 10kHz. If a specific frequency noise component is known, such as switching power supplies frequencies, it is recommended that component values be adjusted and if required, additional filtering be added. Additionally, good general design practices for power plane voltage stability suggests adding bulk capacitance in the local area of all devices.

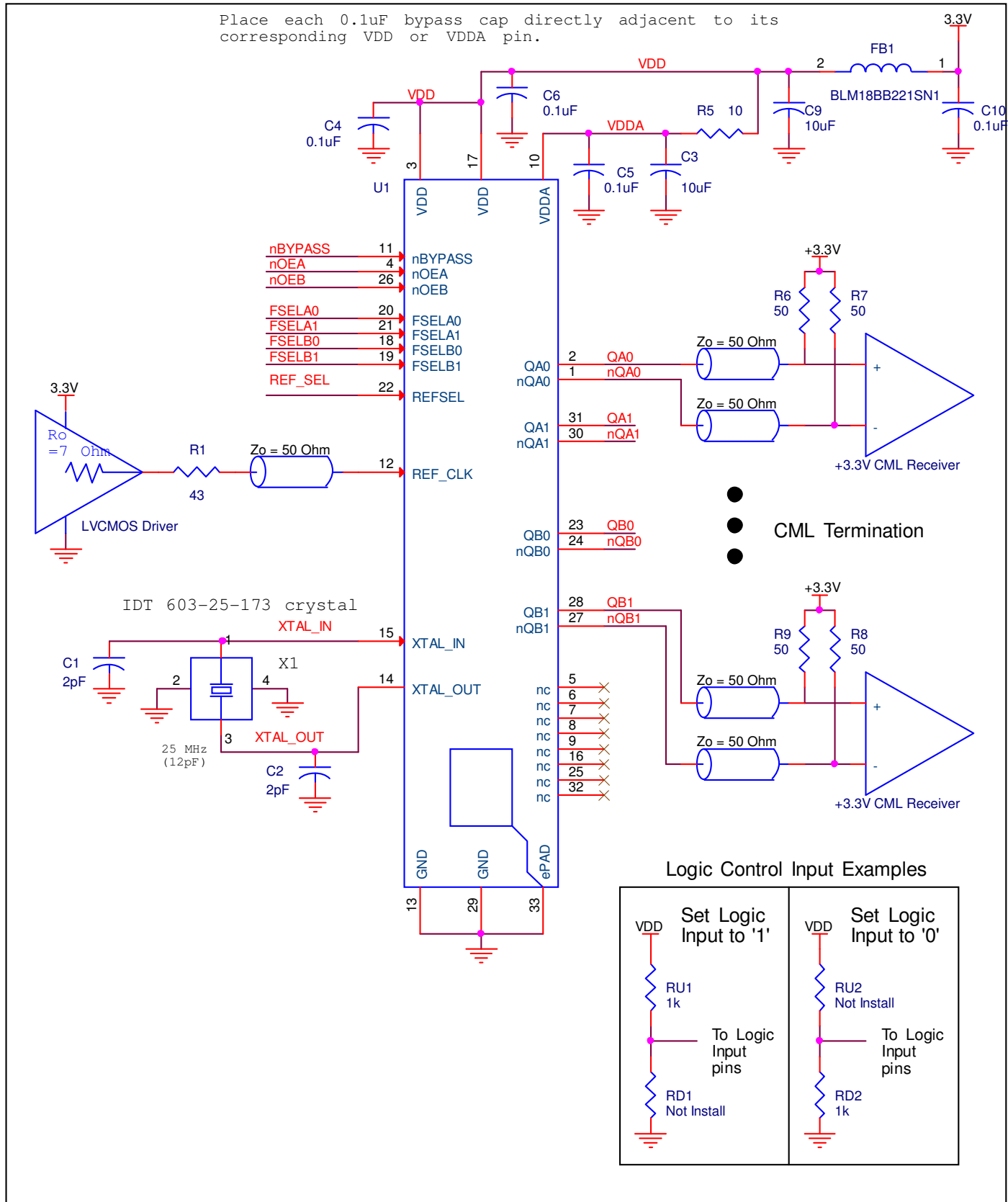


Figure 3. 845264 Schematic Example

Power Considerations

This section provides information on power dissipation and junction temperature for the 845264. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 845264 is the sum of the core power plus the power dissipation into the load. The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipation into the load.

- Power (core)_{MAX} = $V_{DD_MAX} * (I_{DD} + I_{DDA}) = 3.465V * (89mA + 12mA) = \mathbf{349.96mW}$
- Power (outputs)_{MAX} = **35.76mW/Loaded Output pair**
If all outputs are loaded, the total power is $4 * 35.76mW = \mathbf{143.04mW}$

Total Power_{MAX} (3.465V, with all outputs switching) = $349.96mW + 143.04mW = \mathbf{433.01mW}$

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad, and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 43.4°C/W per Table 7 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.493\text{W} * 43.4^\circ\text{C/W} = 106.4^\circ\text{C}. \text{ This is well below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 7. Thermal Resistance θ_{JA} for 32 Lead VFQFN, Forced Convection

| θ_{JA} by Velocity | | | |
|---|----------|----------|----------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 43.4°C/W | 37.9°C/W | 34.0°C/W |

3. Calculations and Equations.

The purpose of this section is to calculate the power dissipation for the CML driver output pair. The CML output circuit and termination are shown in Figure 4.

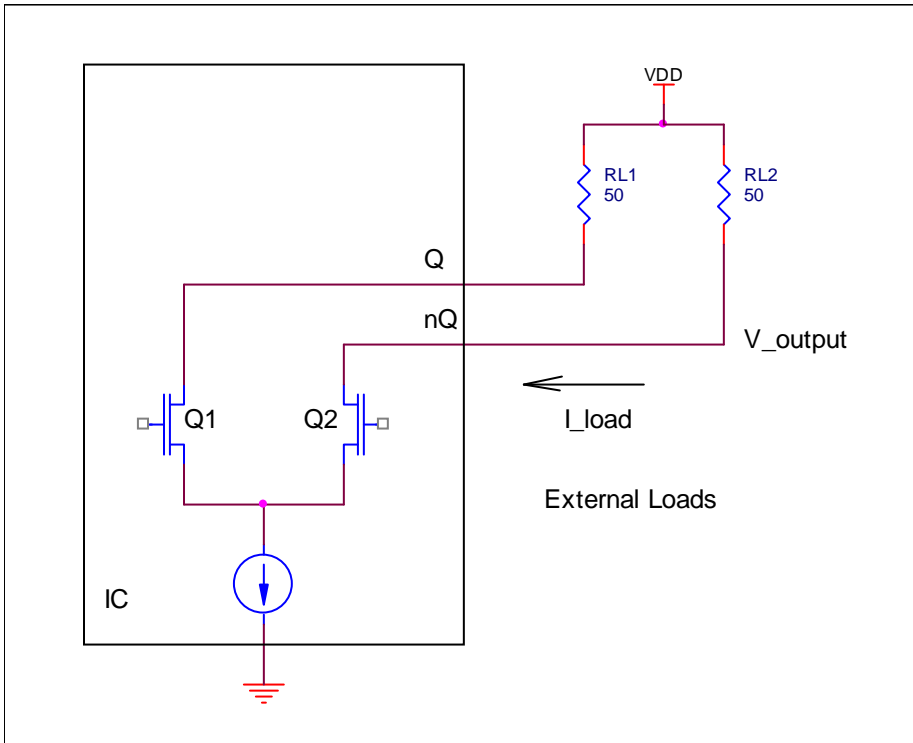


Figure 4. CML Driver Circuit and Termination

To calculate power dissipation per output pair into the load, use the following equations.

Power dissipation when the output driver is logic LOW:

$$\begin{aligned}
 Pd_L &= I_Load * V_Output \\
 &= (V_{OUT_MAX} / R_L) * (V_{DD_MAX} - V_{OUT_MAX}) \\
 &= (600mV / 50\Omega) * (3.465V - 600mV) \\
 &= 34.38mW
 \end{aligned}$$

Power dissipation when the output driver is logic HIGH:

$$\begin{aligned}
 Pd_H &= I_Load * V_Output \\
 &= (0.02V / 50\Omega) * (3.465V - 0.02V) \\
 &= 1.38mW
 \end{aligned}$$

Total Power Dissipation per output pair = Pd_H + Pd_L = **35.76mW**

Reliability Information

Table 8. θ_{JA} vs. Air Flow Table for a 32 lead VFQFN

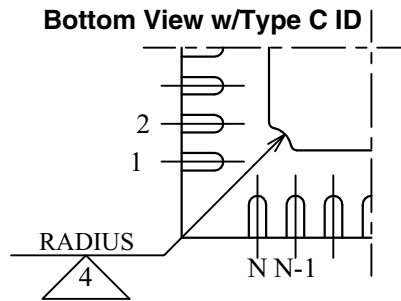
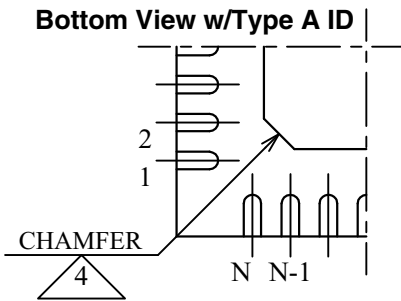
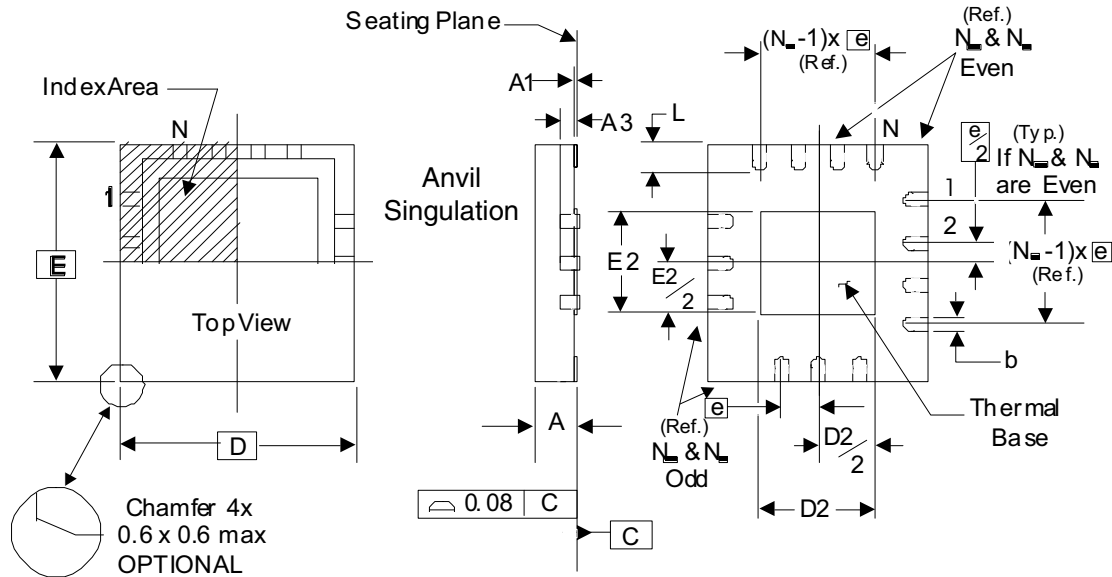
| θ_{JA} vs. Air Flow | | | |
|---|----------|----------|----------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 43.4°C/W | 37.9°C/W | 34.0°C/W |

Transistor Count

The transistor count for the 845264 is: 3216

32 Lead VFQFN Package Outline and Package Dimensions

Package Outline - K Suffix for 32 Lead VFQFN



There are 2 methods of indicating pin 1 corner at the back of the VFQFN package:

1. Type A: Chamfer on the paddle (near pin 1)
2. Type C: Mouse bite on the paddle (near pin 1)

Table 9. Package Dimensions

| JEDEC Variation: VHHD-2/-4 All Dimensions in Millimeters | | | |
|---|------------|---------|---------|
| Symbol | Minimum | Nominal | Maximum |
| N | 32 | | |
| A | 0.80 | | 1.00 |
| $A1$ | 0 | | 0.05 |
| $A3$ | 0.25 Ref. | | |
| b | 0.18 | 0.25 | 0.30 |
| N_D & N_E | 8 | | |
| D & E | 5.00 Basic | | |
| $D2$ & $E2$ | 3.0 | | 3.3 |
| e | 0.50 Basic | | |
| L | 0.30 | 0.40 | 0.50 |

Reference Document: JEDEC Publication 95, MO-220

NOTE: The following package mechanical drawing is a generic drawing that applies to any pin count VFQFN package. This drawing is not intended to convey the actual pin count or pin layout of this device. The pin count and pin-out are shown on the front page. The package dimensions are in Table 9.

Ordering Information

Table 10. Ordering Information

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|-------------------|-------------|--------------------------|--------------------|---------------|
| 845264AKILF | ICS45264AIL | 32 Lead VFQFN, Lead-Free | Tray | -40°C to 85°C |
| 845264AKILFT | ICS45264AIL | 32 Lead VFQFN, Lead-Free | Tape & Reel | -40°C to 85°C |

Revision History Sheet

| Rev | Table | Page | Description of Change | Date |
|-----|-------|------|--|---------|
| B | | 16 | Updated schematic with IDT crystal recommendation. Deleted prefix/suffix from part number throughout the datasheet. Updated header/footer. | 7/20/15 |

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